



Pin Definition:



SOT-26

1. Drain 6. Drain 5. Drain 2. Drain

3. Gate 4. Source

Note:

MSL 1 (Moisture Sensitivity Level) per J-STD-020

	noy i aramot				
	Parameter		Value	Unit	
	V _{DS}	30	V		
	R _{DS(on)} (max)	$V_{GS} = 10V$	24		
		$V_{GS} = 4.5V$	34	mΩ	
	Qg		4.1	nC	

30V N-Channel Power MOSFET

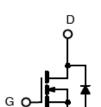
TSM240N03CX6

Features

- Halogen-free
- Improved dV/dt capability
- Fast Switching

Ordering Information Ordering code Package Packing TSM240N03CX6 RFG SOT-26 3kpcs / 7" Reel

Note: Halogen-free according to IEC 61249-2-21 definition



Block Diagram

N-Channel MOSFET

S

Absolute Maximum Ratings (T_c = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	30	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Durin Current	$T_{\rm C} = 25^{\circ}{\rm C}$	I _D	6.5	А
Continuous Drain Current	T _C = 100°C		4.1	А
Pulsed Drain Current (Note 1)	Pulsed Drain Current (Note 1)		26	А
Single Pulse Avalanche Energy $^{(Note 2)}$ Power Dissipation @ T _C = 25°C		E _{AS}	32	mJ
		P _D	1.56	W
Operating Junction Temperature	unction Temperature T _J 150	C°		
Storage Temperature Range		T _{STG}	-55 to +150	C°

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	80	°C/W

Key Parameter Performance





Electrical Specifications (T_c = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV _{DSS}	30			V
	$V_{GS} = 10V, I_D = 6A$	R _{DS(on)}		17	24	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 4A$			22	34	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V _{GS(TH)}	1.2	1.4	2.5	V
	$V_{DS} = 30V, V_{GS} = 0V$	I _{DSS}			1	μA
Zero Gate Voltage Drain Current	V _{DS} = 24V, T _J = 125°C				10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_{D} = 4A$	g _{fs}		6.5		S
Dynamic	1					
Total Gate Charge (Note 3,4)		Q_g		4.1		nC
Gate-Source Charge (Note 3,4)	$V_{DS} = 15V, I_D = 6A,$ $V_{GS} = 4.5V$	Q_{gs}		1		
Gate-Drain Charge (Note 3,4)		Q _{gd}		2.1		
Input Capacitance		C _{iss}		345		pF
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C _{oss}		55		
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		32		
Switching	1					
Turn-On Delay Time (Note 3,4)		t _{d(on)}		2.8		ns
Turn-On Rise Time (Note 3,4)	$V_{DD} = 15V, I_D = 1A,$	t _r		7.2		
Turn-Off Delay Time (Note 3,4)	$V_{GS} = 10V, R_{GEN} = 6\Omega$	t _{d(off)}		15.8		
Turn-Off Fall Time (Note 3,4)		t _f		4.6		
Source-Drain Diode Ratings and Ch	aracteristic				•	
Maximum Continuous Drain-Source	Integral reverse diode in the MOSFET	I _S			6.5	A
Diode Forward Current						
Maximum Pulse Drain-Source Diode		I _{SM}			26	А
Forward Current						
Diode-Source Forward Voltage	$V_{GS} = 0V, I_{S} = 1A$	V_{SD}			1	V

Note:

1. Pulse width limited by safe operating area

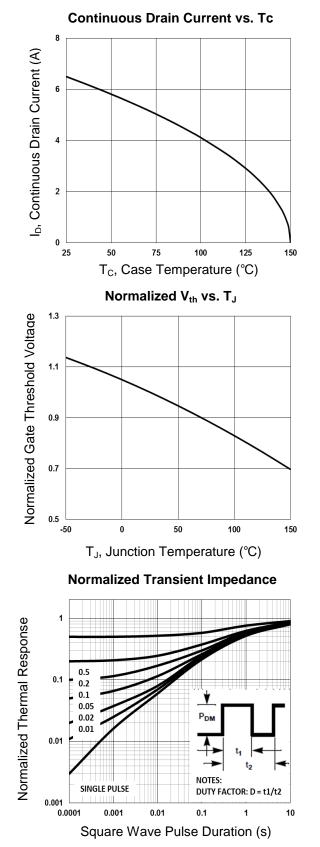
2. L = 1mH, I_{AS} = 8A, V_{DD} = 25V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}$ C

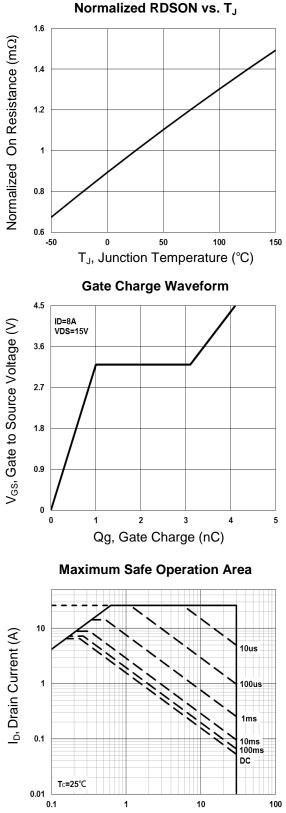
3. Pulse test: pulse width \leq 300µs, duty cycle \leq 2%

4. Switching time is essentially independent of operating temperature.



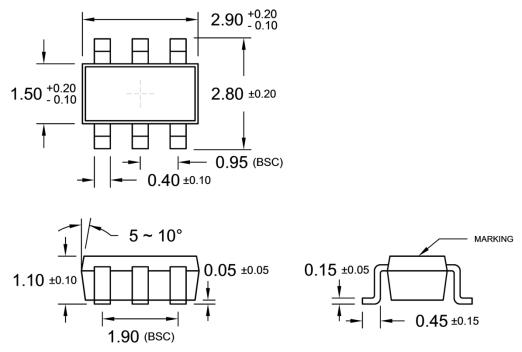
Electrical Characteristics Curve





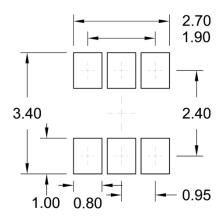


SOT-26 Mechanical Drawing



Unit: Millimeters

SUGGESTED PAD LAYOUT (Unit: Millimeters)



Marking Diagram



- 24 = Device Code
- Y = Year Code
- M = Month Code for Halogen Free Product
 (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)
- L = Lot Code





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